

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD2148

DESCRIPTION

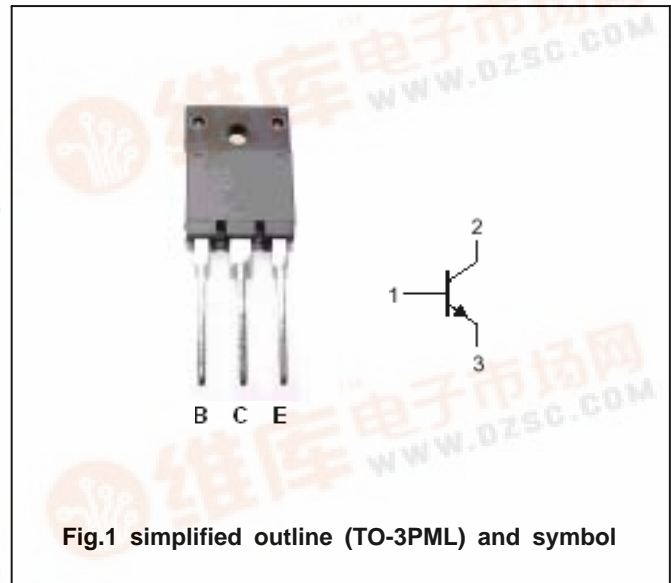
- With TO-3PML package
- High voltage ,high speed
- Low collector saturation voltage

APPLICATIONS

- High speed switching power supply output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (T_a=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	700	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		8	A
I _{CM}	Collector current-peak		16	A
I _B	Base current		4	A
P _C	Collector power dissipation	T _C =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA , I _B =0	700			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA , I _C =0	5			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =7A ; I _B =1.4A			5.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =7A ; I _B =1.4A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	8			
h _{FE-2}	DC current gain	I _C =7A ; V _{CE} =5V	4			

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PACKAGE OUTLINE

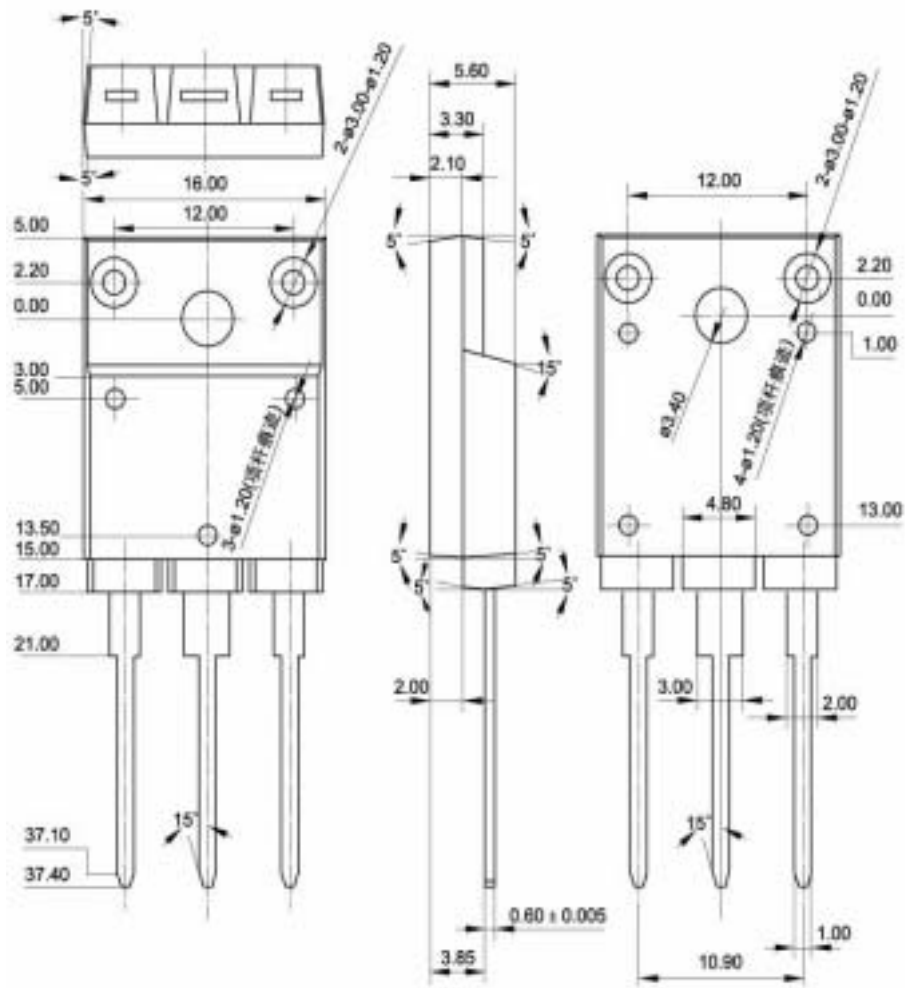


Fig.2 outline dimensions(unindicated tolerance: ± 0.10 mm)